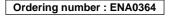
#### 查询FW217供应商





## SANYO Semiconductors DATA SHEET

## N-Channel Silicon MOSFET

# FW217 — General-Purpose Switching Device Applications

## **Features**

- Motor drive applications.
- 4V drive.

## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Drain-to-Source Voltage	VDSS		35	V	
Gate-to-Source Voltage	VGSS	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	±20	V	
Drain Current (DC)	ID		6	А	
Drain Current (PW≤10s)	ID	Duty cycle≤1%	6.3	А	
Drain Current (PW≤10µs)	IDP	Duty cycle≤1%	24	А	
Allowable Power Dissipation	PD	Mounted on a ceramic board (2000mm <sup>2</sup> X0.8mm) 1unit, PW≤10s	1.8	W	
Total Dissipation	PT	Mounted on a ceramic board (2000mm <sup>2</sup> X0.8mm), PW≤10s	2.2	W	
Channel Temperature	Tch		150	°C	
Storage Temperature	Tstg		-55 to +150	°C	

## Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	1.00	Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35	and We	0	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V		1000	1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		2.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =6A	4.0	6.6		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=6A, VGS=10V		33	44	mΩ
	R <sub>DS</sub> (on)2	ID=3A, VGS=4V		65	91	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		630		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		120		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		80		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		12	25.0	ns
Rise Time	tr	See specified Test Circuit.		85	W.c.	ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.	The Course I	42	01.5	ns
Fall Time	tf	See specified Test Circuit.		42		ns

Marking : W217

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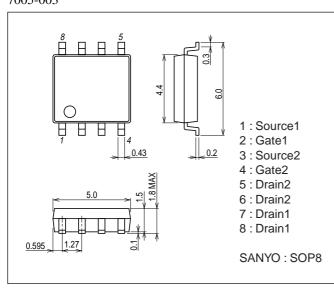
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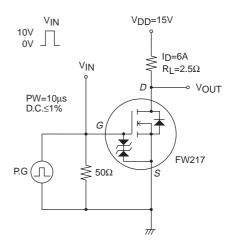
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		12		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		2.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		1.8		nC
Diode Forward Voltage	V <sub>SD</sub>	IS=6A, VGS=0V		0.87	1.2	V

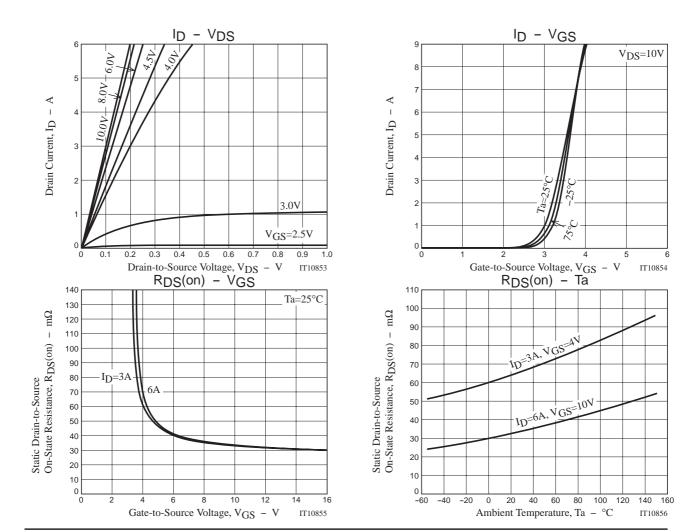
## **Package Dimensions**

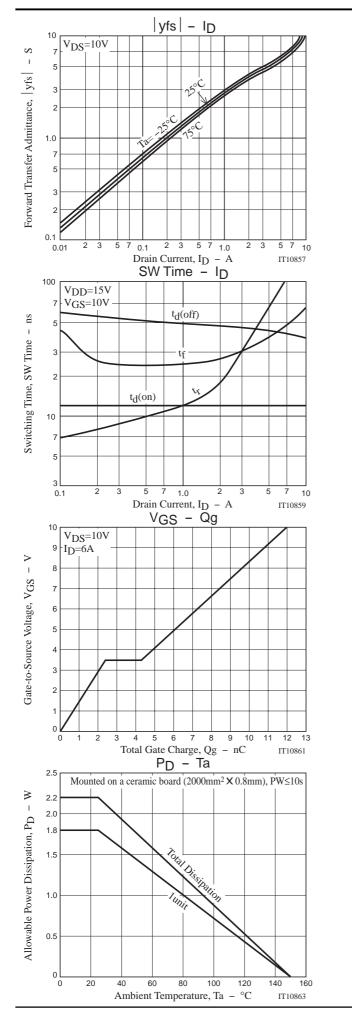
unit : mm 7005-003

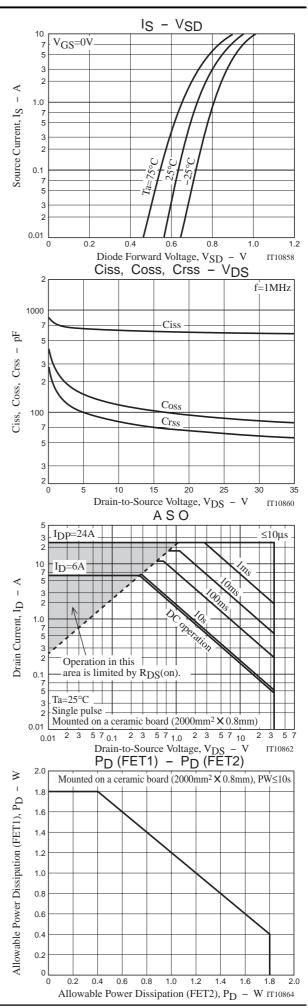


## **Switching Time Test Circuit**









Note on usage : Since the FW217 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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